KSU13003HR

SemiHow
Know-How for Semiconductor

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Switch Mode series NPN silicon Power Transistor

- High Voltage, High Speed Switching
- Suitable for switching regulator, inverters motor controls

2 Amperes
NPN Silicon Power Transistor
25 Watts

TO-251
1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings TC=25℃ unless otherwise noted

CHARACTERISTICS	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	900	V
Collector-Emitter Voltage	V_{CEO}	530	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current(DC)	I_C	2	A
Collector Current(Pulse)	I_{CP}	4	A
Base Current	I_B	1	A
Collector Dissipation(Tc=25℃)	P_C	25	W
Storage Temperature	T_{STG}	-55~150	℃
Max. Operating Junction Temperature	T_J	150	℃

Electrical Characteristics TC=25℃ unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	V_{CBO}	I_C=500μA, I_E=0	900			V
Collector-Emitter Breakdown Voltage	V_{CEO}	I_C=10mA, I_B=0	530			V
Emitter Cut-off Current	I_{EBO}	V_{EB}=9V,I_C=0			10	μA
*DC Current Gain	h_{FE1} h_{FE2}	V_{CE}=10V,I_C=0.4A V_{CE}=10V,I_C=1A	20 6		40	
*Collector-Emitter Saturation Voltage	V_{CE}(sat)	I_C=0.5A,I_B=0.1A I_C=1.5A,I_B=0.5A			0.8 2.5	V V
*Base-Emitter Saturation Voltage	V_{BE}(sat)	I_C=0.5A,I_B=0.1A			1.0	V
Output Capacitance	C_{ob}	V_{CB}=10V, f=0.1MHz		21		pF
Current Gain Bandwidth Product	f_T	V_{CE}=10V,I_C=0.1A	4			MHz
Turn on Time	t_{on}	Vcc=125V, Ic=2A I_{B1}=0.2A, I_{B2}= -0.2A R_L=125Ω			1.1	μs
Storage Time	t_{stg}				4.0	μs
Fall Time	t_F				0.7	μs

* Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Note.

hFE1 Classification	R	20 ~ 30
	O	25 ~ 35
	Y	30 ~ 40

Package Mark information.

S HR **1 3 0 0 3** **Y W W Z**	S	SemiHow Symbol
	YWW	Y; year code, WW; week code
	Z	hFE1 Classification

Typical Characteristics

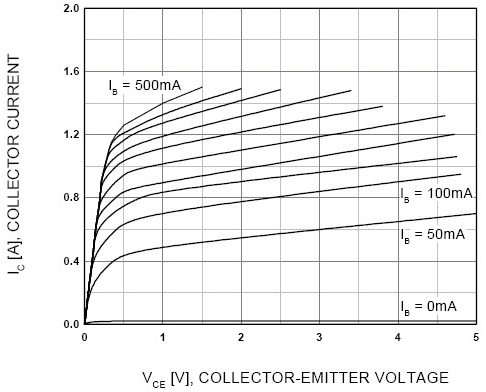

Figure 1. Static Characteristic

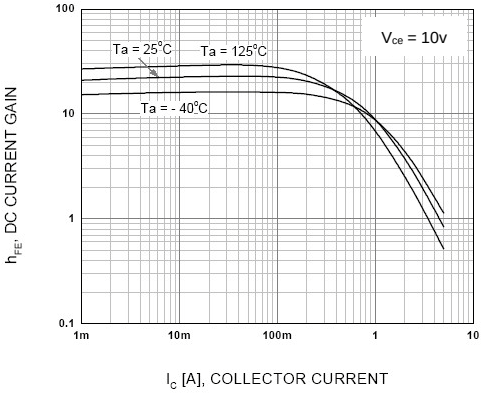

Figure 2. DC current Gain

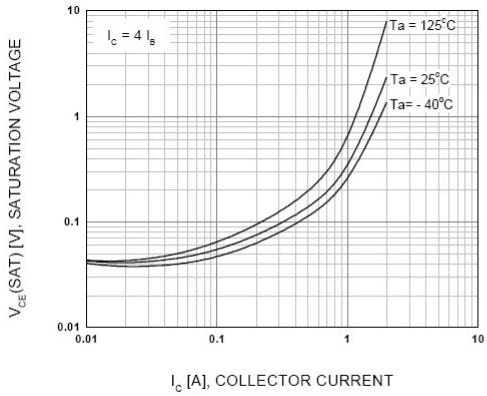

Figure 3. Collector-Emitter Saturation Voltage

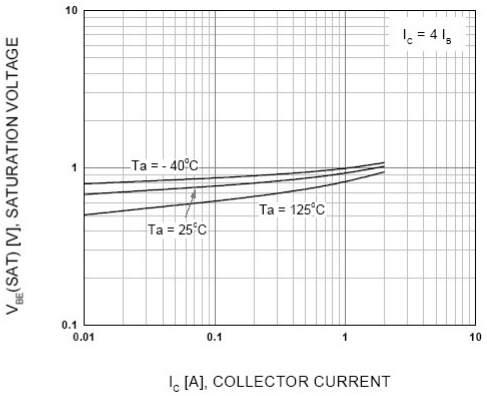

Figure 4. Base-Emitter Saturation Voltage

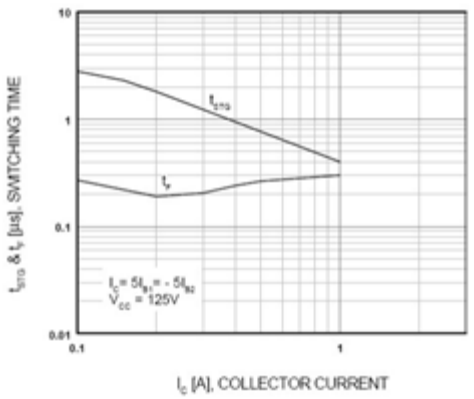

Figure 5. Resistive Load Switching Time

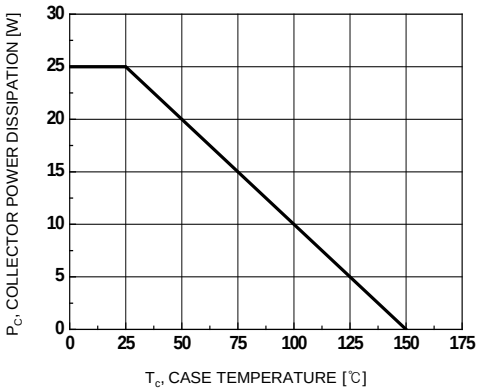

Figure 6. Power Derating

Typical Characteristics

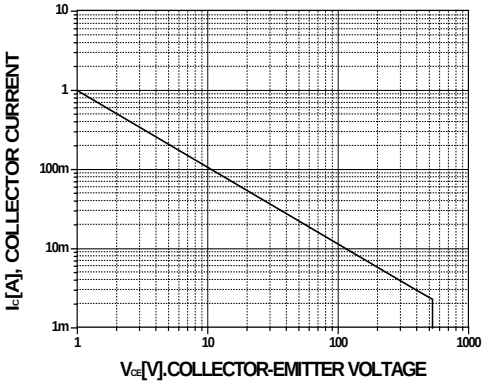

Figure 7. Forward Bias Safe Operating Area

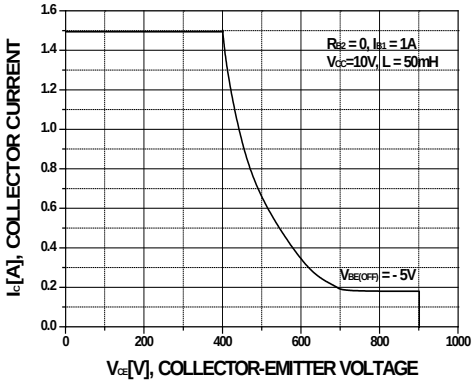

Figure 8. Reverse Bias Safe Operating Area

Package Dimension

TO-251